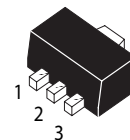


PNP Plastic-Encapsulate Transistors

(Pb) Lead(Pb)-Free

SOT-89



1. BASE
2. COLLECTOR
3. EMITTER

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCBO	-40	Vdc
Collector-Base Voltage	VCEO	-32	Vdc
Emitter-Base Voltage	VEBO	-5.0	Vdc
Collector Current	IC	-1.0	A(DC)
	ICP	-2.0	A (Pulse)*
Collector Power Dissipation	PC <small>www.DataSheet4U.com</small>	0.5	W
Junction Temperature, Storage Temperature	Tj, Tstg	150, -55 to +150	°C

* Single pulse Pw = 100ms

DEVICE MARKING

2SB1132P=BAP, 2SB1132Q=BAQ, 2SB1132R=BAR

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
Collector-Base Breakdown Voltage (IC= -50 uAdc, IE=0)	V(BR)CBO	-40	-	Vdc
Collector-Emitter Breakdown Voltage (IC= -1 mAdc, IB=0)	V(BR)CEO	-32	-	Vdc
Emitter-Base Breakdown Voltage (IE= -50 uAdc, IC=0)	V(BR)EBO	-5.0	-	Vdc
Collector Cutoff Current (VCB= -20Vdc, IE=0)	ICBO	-	-0.5	uAdc
Emitter Cutoff Current (VEB= -4.0 Vdc, IC=0)	IEBO	-	-0.5	uAdc

2SB1132 **WEITRON****ELECTRICAL CHARACTERISTICS** ($T_A=25^{\circ}\text{C}$ unless otherwise noted) (Continued)

Characteristics	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS

DC Current Gain ($I_C = -100\text{ mAdc}, V_{CE} = -3\text{ Vdc}$)	h_{FE}	82	-	390	-
Collector-Emitter Saturation Voltage ($I_C = -500\text{ mAdc}, I_B = -50\text{ mAdc}$)	$V_{CE(sat)}$	-	-	-0.5	Vdc
Transition Frequency ($I_C = -50\text{ mAdc}, V_{CE} = -5\text{ Vdc}, f = 30\text{ MHz}$)	f_T	-	150	-	MHz
Collector Output Capacitance ($I_E = 0, V_{CB} = -10\text{ Vdc}, f = 1\text{ MHz}$)	C_{ob}	-	20	30	PF

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390

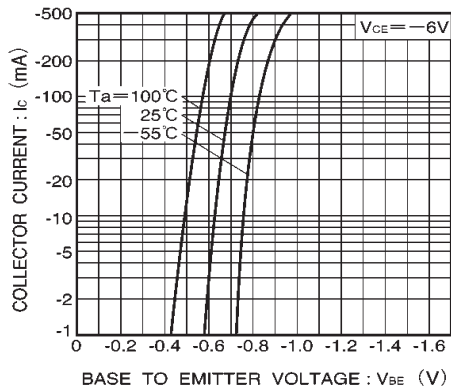


FIG.1 Grounded emitter propagation characteristics

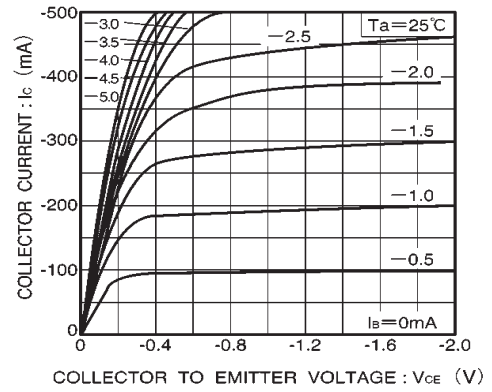


FIG.2 Grounded emitter output characteristics

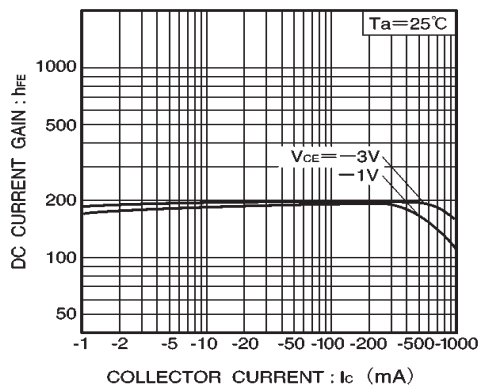


FIG.3 DC current gain vs. collector current (I)

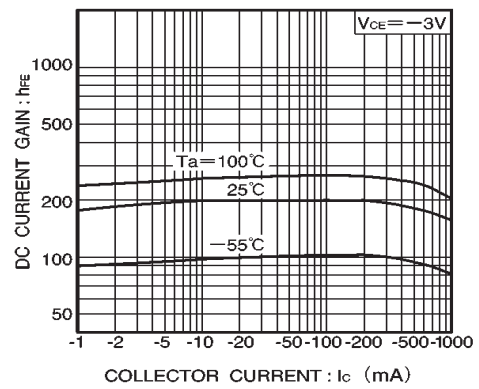


FIG.4 DC current gain vs. collector current (II)

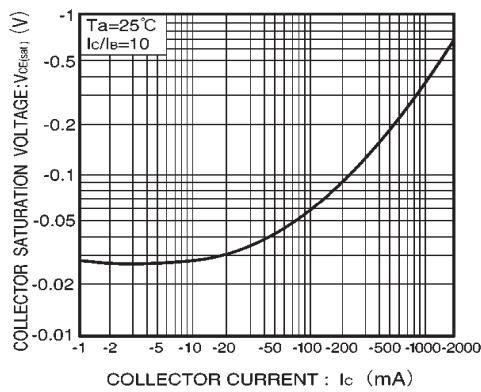


FIG.5 Collector-emitter saturation voltage vs. collector current

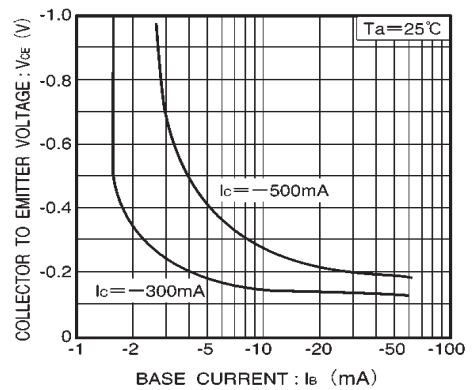


FIG.6 Collector-emitter saturation voltage vs. base current

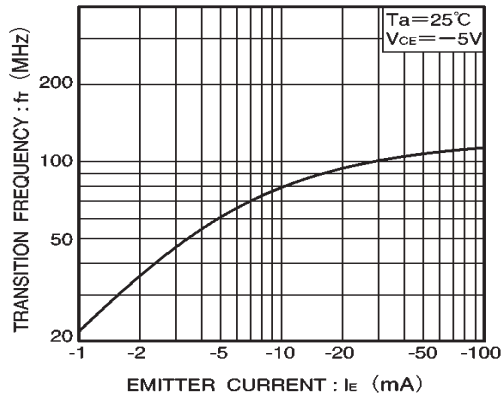


FIG.7 Gain bandwidth product vs. emitter current

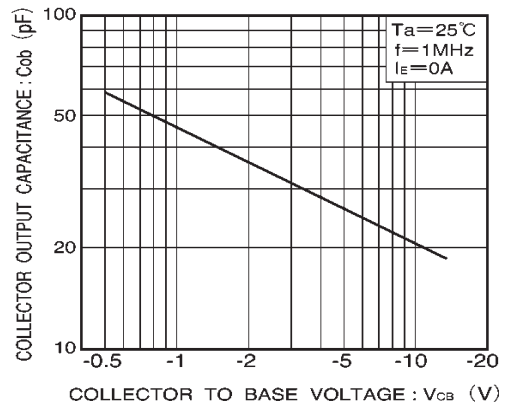


FIG.8 Collector output capacitance vs. collector-base voltage

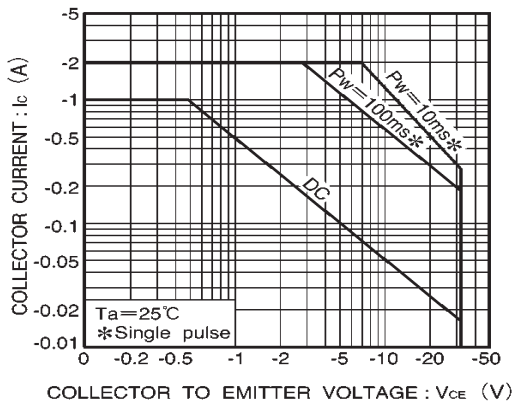


FIG.9 Safe operation area

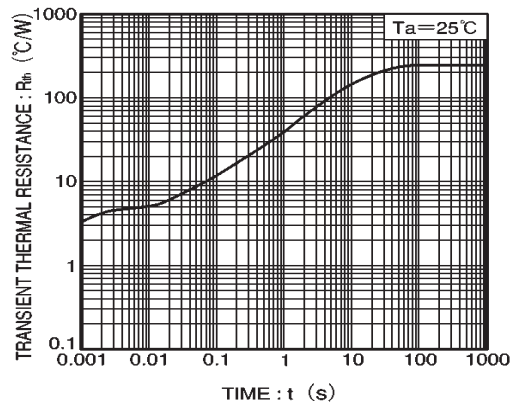
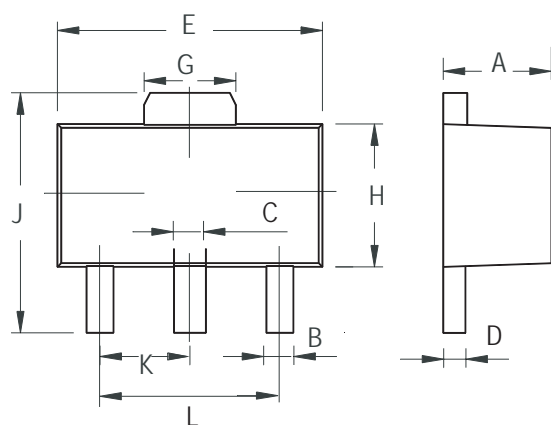


FIG.10 Transient thermal resistance

SOT-89 Outline Dimensions

unit:mm



SOT-89		
Dim	Min	Max
A	1.400	1.600
B	0.320	0.520
C	0.360	0.560
D	0.350	0.440
E	4.400	4.600
G	1.400	1.800
H	2.300	2.600
J	3.940	4.250
K	1.500TYP	
L	2.900	3.100